

# EL5175, EL5375

#### 550MHz Differential Line Receivers

FN7306 Rev.8.00 Aug 7, 2020

The EL5175 and EL5375 are single and triple high bandwidth amplifiers designed to extract the difference signal from noisy environments. They are primarily targeted for applications such as receiving signals from twisted-pair lines or any application where common mode noise injection is likely to occur.

The EL5175 and EL5375 are stable for a gain of one and requires two external resistors to set the voltage gain for each channel.

The output common mode level is set by the reference pin  $(V_{REF})$ , which has a -3dB bandwidth of over 450MHz. Generally, this pin is grounded but it can be tied to any voltage reference.

The output can deliver a maximum of ±60mA and is short circuit protected to withstand a temporary overload condition.

The EL5175 is available in the 8 Ld SOIC and 8 Ld MSOP packages and the EL5375 in the 24 Ld QSOP package. All are specified for operation over the full -40°C to +85°C temperature range.

#### Related Literature

For a full list of related documents, visit our website:

• EL5175, EL5375 device pages

#### Features

- · Differential input range ±2.3V
- · 550MHz 3dB bandwidth
- 900V/µs slew rate
- 60mA maximum output current
- Single 5V or dual ±5V supplies
- · Low power, 9.6mA per channel
- · Pb-free available (RoHS compliant)

#### **Applications**

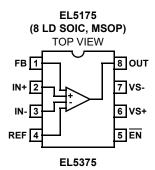
- · Twisted-pair receivers
- · Differential line receivers
- · VGA over twisted-pair
- · Differential to single-ended amplification
- · Reception of analog signals in a noisy environment

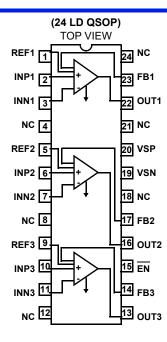
## **Ordering Information**

PART NUMBER (Notes 2, 3)	PART MARKING	TAPE AND REEL (UNITS) (Note 1)	PACKAGE (RoHS Compliant)	PKG. DWG.#
EL5175ISZ	5175ISZ	-	8 Ld SOIC (150 mil)	M8.15E
EL5175ISZ-T7	5175ISZ	1k	8 Ld SOIC (150 mil)	M8.15E
EL5175ISZ-T13	5175ISZ	2.5k	8 Ld SOIC (150 mil)	M8.15E
EL5175IYZ	BAAAB	-	8 Ld MSOP (3.0mm)	M8.118A
EL5175IYZ-T7	BAAAB	1.5k	8 Ld MSOP (3.0mm)	M8.118A
EL5175IYZ-T13	BAAAB	2.5k	8 Ld MSOP (3.0mm)	M8.118A
EL5375IUZ	EL5375IUZ	-	24 Ld QSOP (150 mil)	MDP0040
EL5375IUZ-T7	EL5375IUZ	1k	24 Ld QSOP (150 mil)	MDP0040
EL5375IUZ-T13	EL5375IUZ	2.5k	24 Ld QSOP (150 mil)	MDP0040

- 1. See <u>TB347</u> for details about reel specifications.
- 2. These Pb-free plastic packaged products employ special Pb-free material sets, molding compounds/die attach materials, and 100% matte tin plate plus anneal (e3 termination finish, which is RoHS compliant and compatible with both SnPb and Pb-free soldering operations). Pb-free products are MSL classified at Pb-free peak reflow temperatures that meet or exceed the Pb-free requirements of IPC/JEDEC J STD-020.
- 3. or Moisture Sensitivity Level (MSL), see the <u>EL5175</u>, <u>EL5375</u> device pages. For more information about MSL, see <u>TB363</u>.

## **Pinouts**





# Pin Descriptions

EL5175	EL5375	PIN NAME	PIN FUNCTION
1		FB	Feedback input
2		IN+	Non-inverting input
3		IN-	Inverting input
4		REF	Sets the common mode output voltage level to V <sub>REF</sub>
5		EN	Enabled when this pin is floating or the applied voltage $\leq V_S + -1.5$
6		VS+	Positive supply voltage
7		VS-	Negative supply voltage
8		OUT	Output voltage
	1, 5, 9	REF1, REF2, REF3	Reference input, controls common-mode output voltage
	2, 6, 10	INP1, INP2, INP3	Non-inverting inputs
	3, 7, 11	INN1, INN2, INN3	Inverting inputs
	4, 8, 12, 18, 21, 24	NC	No connect, grounded for best crosstalk performance
	22, 16, 13	OUT1, OUT2, OUT3	Non-inverting outputs
	23, 17, 14	FB1, FB2, FB3	Feedback from outputs
	15	EN	Enabled when this pin is floating or the applied voltage $\leq V_S + -1.5$
	19	VSN	Negative supply
	20	VSP	Positive supply

### **Absolute Maximum Ratings** (T<sub>A</sub> = +25°C)

## 

#### **Thermal Information**

Operating Junction Temperature	+135°C
Ambient Operating Temperature	40°C to +85°C
Storage Temperature Range	65°C to +150°C
Power Dissipation	See Curves
Pb-free reflow profile	see <u>TB493</u>

CAUTION: Do not operate at or near the maximum ratings listed for extended periods of time. Exposure to such conditions can adversely impact product reliability and result in failures not covered by warranty.

IMPORTANT NOTE: All parameters having Min/Max specifications are guaranteed. Typ values are for information purposes only. Unless otherwise noted, all tests are at the specified temperature and are pulsed tests, therefore:  $T_J = T_C = T_A$ 

**Electrical Specifications**  $V_S$ + = +5V,  $V_S$ - = -5V,  $T_A$  = +25°C,  $V_{IN}$  = 0V,  $R_L$  = 500 $\Omega$ ,  $R_F$  = 0,  $R_G$  = OPEN,  $C_L$  = 2.7pF, Unless Otherwise Specified.

PARAMETER	DESCRIPTION	CONDITIONS	MIN	TYP	MAX	UNIT
AC PERFORMA	NCE			•		"
BW	-3dB Bandwidth	A <sub>V</sub> = 1, C <sub>L</sub> = 2.7pF		550		MHz
		A <sub>V</sub> = 2, R <sub>F</sub> = 806, C <sub>L</sub> = 2.7pF		190		MHz
		A <sub>V</sub> = 10, R <sub>F</sub> = 806, C <sub>L</sub> = 2.7pF		20		MHz
BW	± 0.1dB Bandwidth	A <sub>V</sub> = 1, C <sub>L</sub> = 2.7pF		60		MHz
SR	Slew Rate	$V_{OUT} = 3V_{P-P}$ , 20% to 80%, $R_L = 100\Omega$		600		V/µs
		$V_{OUT} = 3V_{P-P}$ , 20% to 80%, $R_L = 500\Omega$		900		V/µs
t <sub>STL</sub>	Settling Time to 0.1%	V <sub>OUT</sub> = 2V <sub>P-P</sub>		10		ns
tovr	Output Overdrive Recovery Time			20		ns
GBWP	Gain Bandwidth Product			200		MHz
V <sub>REF</sub> BW (-3dB)	V <sub>REF</sub> -3dB Bandwidth	A <sub>V</sub> = 1, C <sub>L</sub> = 2.7pF		450		MHz
V <sub>REF</sub> SR	V <sub>REF</sub> Slew Rate	V <sub>OUT</sub> = 2V <sub>P-P</sub> , 20% to 80%		1000		V/µs
V <sub>N</sub>	Input Voltage Noise	At f = 10kHz		21		nV/√Hz
I <sub>N</sub>	Input Current Noise	At f = 10kHz		2.7		pA/√Hz
HD2	Second Harmonic Distortion	V <sub>OUT</sub> = 1V <sub>P-P</sub> , 5MHz		-70		dBc
HD2	Second Harmonic Distortion	V <sub>OUT</sub> = 1V <sub>P-P</sub> , 5MHz		-66		dBc
HD3	Third Harmonic Distortion	V <sub>OUT</sub> = 1V <sub>P-P</sub> , 5MHz		-94		dBc
HD3	Third Harmonic Distortion	V <sub>OUT</sub> = 1V <sub>P-P</sub> , 5MHz		-84		dBc
dG	Differential Gain at 3.58MHz	R <sub>L</sub> = 150Ω, A <sub>V</sub> = 2		0.1		%
dθ	Differential Phase at 3.58MHz	R <sub>L</sub> = 150Ω, A <sub>V</sub> = 2		0.1		0
e <sub>S</sub>	Channel Separation (EL5375)	At f = 100kHz		90		dB
INPUT CHARAC	TERISTICS				•	-
V <sub>OS</sub>	Input Referred Offset Voltage	EL5175		-3	±40	mV
		EL5375		-3	±30	mV
I <sub>IN</sub>	Input Bias Current (V <sub>IN</sub> , V <sub>INB</sub> , V <sub>REF</sub> )		-25	-12.5	-6	μA
R <sub>IN</sub>	Differential Input Resistance			150		kΩ
C <sub>IN</sub>	Differential Input Capacitance			1		pF
DMIR	Differential Mode Input Range		±2.1	±2.3	±2.5	V
CMIR	Common Mode Input Range at V <sub>IN</sub> +, V <sub>IN</sub> -		-4.3		+3.3	V
V <sub>REFIN</sub> +	Reference Input - Positive	V <sub>IN</sub> + = V <sub>IN</sub> - = 0V	3.3	3.5		V
V <sub>REFIN</sub> -	Reference Input - Negative	V <sub>IN</sub> + = V <sub>IN</sub> - = 0V		-3.9	-3.6	V



# 

PARAMETER	DESCRIPTION	CONDITIONS	MIN	TYP	MAX	UNIT
CMRR	Input Common Mode Rejection Ratio	V <sub>IN</sub> = ±2.5V	75	95		dB
Gain	Gain Accuracy	EL5175, V <sub>IN</sub> = 1V	0.979	0.994	1.009	V
		EL5375, V <sub>IN</sub> = 1V	0.977	0.992	1.007	V
OUTPUT CHAR	ACTERISTICS	1				
V <sub>OUT</sub>	Positive Output Voltage Swing	$R_L = 500\Omega$ to GND	3.3	3.54		V
	Negative Output Voltage Swing	$R_L = 500\Omega$ to GND		-3.95	-3.6	V
I <sub>OUT</sub> (Max)	Maximum Output Current	R <sub>L</sub> = 10Ω	±40	±67		mA
R <sub>OUT</sub>	Output Impedance			130		mΩ
SUPPLY			+		+	
V <sub>SUPPLY</sub>	Supply Operating Range	V <sub>S</sub> + to V <sub>S</sub> -	4.75		11	V
I <sub>S</sub> (ON)	Power Supply Current Per Channel - Enabled		8	9.6	11	mA
I <sub>S (OFF)</sub> +	Positive Power Supply Current - Disabled	EN pin tied to 4.8V, EL5175		80	100	μA
		EN pin tied to 4.8V, EL5375		1.7	5	μA
Is (OFF)-	Negative Power Supply Current - Disabled		-150	-120	-90	μΑ
PSRR	Power Supply Rejection Ratio	V <sub>S</sub> from ±4.5V to ±5.5V	45	56		dB
ENABLE						
t <sub>EN</sub>	Enable Time			80		ns
t <sub>DS</sub>	Disable Time			1.2		μs
V <sub>IH</sub>	EN Pin Voltage for Power-up				V <sub>S</sub> + - 1.5	V
V <sub>IL</sub>	EN Pin Voltage for Shutdown		V <sub>S</sub> + - 0.5			V
I <sub>IH-EN</sub>	EN Pin Input Current High Per Channel	At V <sub>EN</sub> = 5V		40	60	μΑ
I <sub>IL-EN</sub>	EN Pin Input Current Low Per Channel	At V <sub>EN</sub> = 0V	-10	-3		μΑ
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## **Connection Diagrams**

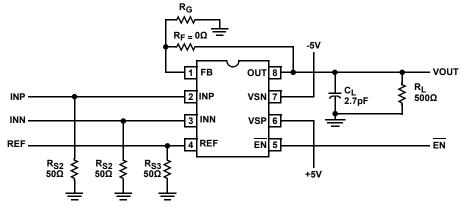


FIGURE 1. EL5175

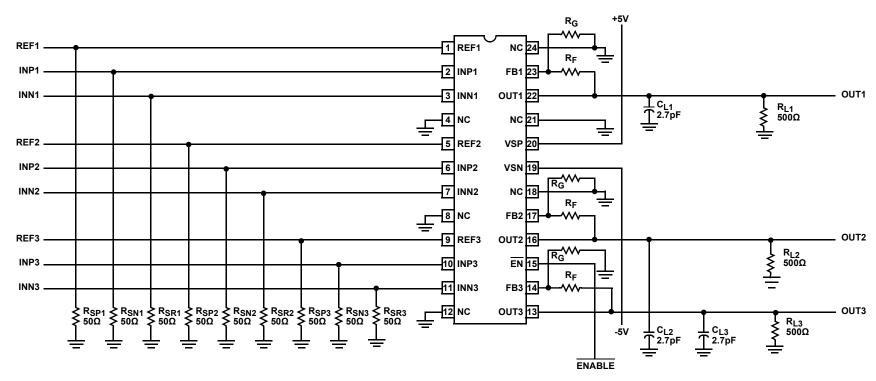


FIGURE 2. EL5375

### **Typical Performance Curves**

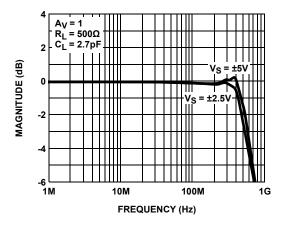


FIGURE 3. FREQUENCY RESPONSE vs SUPPLY VOLTAGE

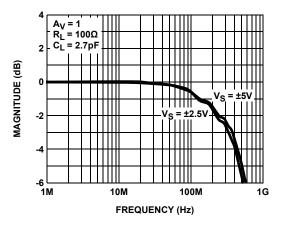


FIGURE 4. FREQUENCY RESPONSE vs SUPPLY VOLTAGE

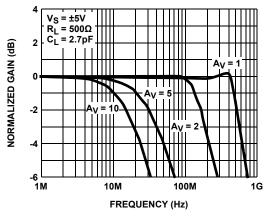


FIGURE 5. FREQUENCY RESPONSE vs VARIOUS GAIN

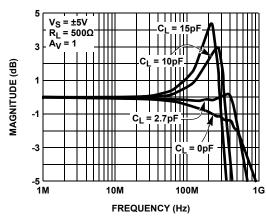


FIGURE 6. FREQUENCY RESPONSE vs CL

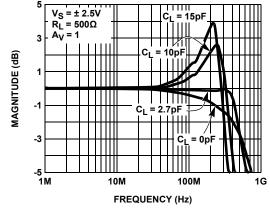


FIGURE 7. FREQUENCY RESPONSE vs CL

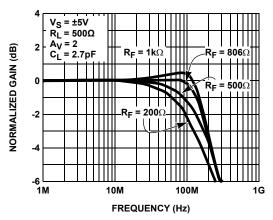


FIGURE 8. FREQUENCY RESPONSE FOR VARIOUS RF

## Typical Performance Curves (Continued)

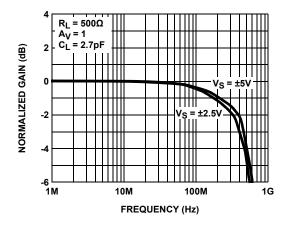


FIGURE 9. FREQUENCY RESPONSE FOR VREF

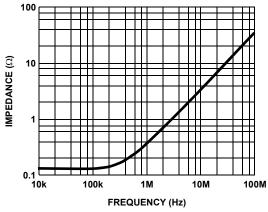


FIGURE 11. OUTPUT IMPEDANCE vs FREQUENCY

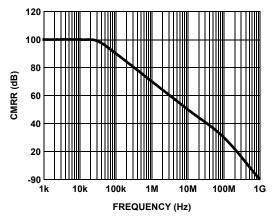


FIGURE 13. CMRR vs FREQUENCY

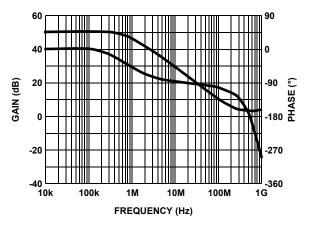


FIGURE 10. OPEN LOOP GAIN

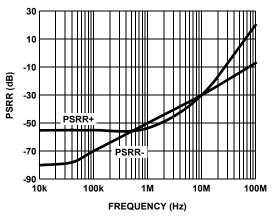


FIGURE 12. PSRR vs FREQUENCY

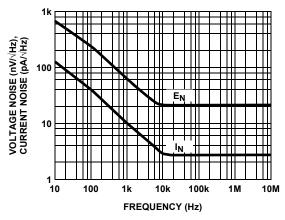


FIGURE 14. VOLTAGE AND CURRENT NOISE vs FREQUENCY

## Typical Performance Curves (Continued)

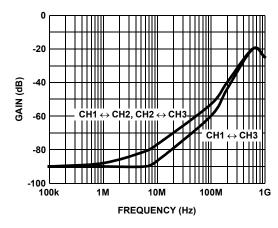


FIGURE 15. CHANNEL ISOLATION vs FREQUENCY (EL5375 ONLY)

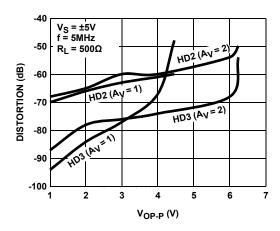


FIGURE 16. HARMONIC DISTORTION vs OUTPUT VOLTAGE

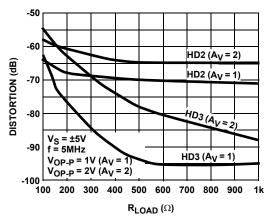


FIGURE 17. HARMONIC DISTORTION vs LOAD RESISTANCE

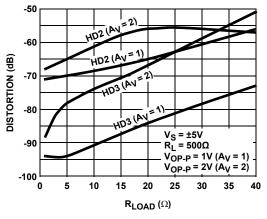


FIGURE 18. HARMONIC DISTORTION vs FREQUENCY

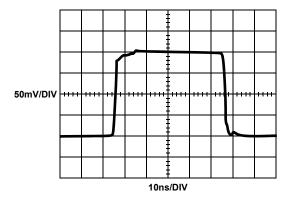


FIGURE 19. SMALL SIGNAL TRANSIENT RESPONSE

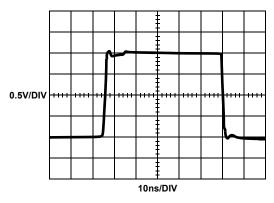


FIGURE 20. LARGE SIGNAL TRANSIENT RESPONSE

## Typical Performance Curves (Continued)

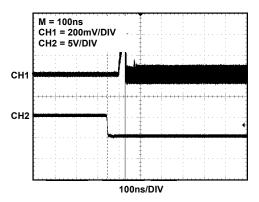


FIGURE 21. ENABLED RESPONSE

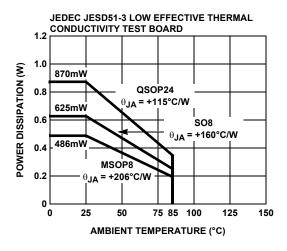


FIGURE 23. PACKAGE POWER DISSIPATION VS AMBIENT TEMPERATURE

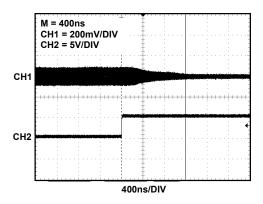


FIGURE 22. DISABLED RESPONSE

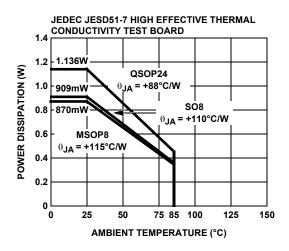
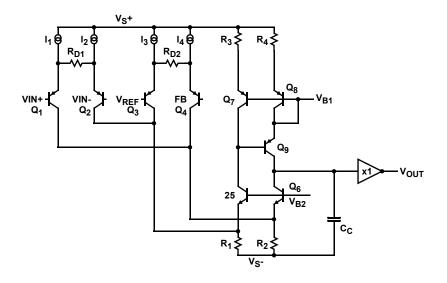


FIGURE 24. PACKAGE POWER DISSIPATION VS AMBIENT TEMPERATURE

## Simplified Schematic



# Description of Operation and Application Information

#### **Product Description**

The EL5175 and EL5375 are wide bandwidth, low power and single/differential ended to single-ended output amplifiers. The EL5175 is a single channel differential to single-ended amplifier. The EL5375 is a triple channel differential to single ended amplifier. The EL5175 and EL5375 are internally compensated for closed loop gain of +1 orgreater. Connected in gain of 1 and driving a  $500\Omega$  load, the EL5175 and EL5375 have a -3dB bandwidth of 550 MHz. Driving a  $150\Omega$  load at gain of 2, the bandwidth is about 130MHz. The bandwidth at the REF input is about 450 MHz. The EL5175 and EL5375 is available with a power-down feature to reduce the power while the amplifier is disabled.

#### Input, Output and Supply Voltage Range

The EL5175 and EL5375 have been designed to operate with a single supply voltage of 5V to 10V or a split supplies with its total voltage from 5V to 10V. The amplifiers have an input common mode voltage range from -4.3V to 3.3V for ±5V supply. The differential mode input range (DMIR) between the two inputs is approximately -2.3V to +2.3V. The input voltage range at the REF pin is from -3.6V to 3.3V. If the input common mode or differential mode signal is outside the above-specified ranges, it will cause the output signal to become distorted.

The output of the EL5175 and EL5375 can swing from -3.9V to 3.5V at  $500\Omega$  load at  $\pm 5V$  supply. As the load resistance becomes lower, the output swing is reduced respectively.

#### **Overall Gain Settings**

The gain setting for the EL5175 and EL5375 is similar to the conventional operational amplifier. The output voltage is equal to the difference of the inputs plus  $V_{REF}$  and then times the gain.

$$V_{O} = (V_{IN} + -V_{IN} - +V_{REF}) \times \left(1 + \frac{R_{F}}{R_{G}}\right)$$
 (EQ. 1)

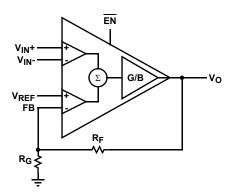


FIGURE 25.

#### Choice of Feedback Resistor and Gain Bandwidth Product

For applications that require a gain of +1, no feedback resistor is required. Just short the OUT+ pin to FBP pin and OUT- pin to FBN pin. For gains greater than +1, the feedback resistor forms a pole with the parasitic capacitance at the inverting input. As this pole becomes smaller, the amplifier's phase margin is reduced. This causes ringing in the time domain and peaking in the frequency domain. Therefore,  $R_{\text{F}}$  has some maximum value that should not be exceeded for optimum performance. If a large value of  $R_{\text{F}}$  must be used, a small capacitor in the few Pico farad range in parallel with  $R_{\text{F}}$  can help to reduce the ringing and peaking at the expense of reducing the bandwidth.

The bandwidth of the EL5175 and EL5375 depends on the load and the feedback network.  $R_{\textrm{F}}$  and  $R_{\textrm{G}}$  appear in parallel with the load for gains other than +1. As this combination gets smaller, the bandwidth falls off. Consequently,  $R_{\textrm{F}}$  also has a minimum value that should not be exceeded for optimum bandwidth performance. For gain of +1,  $R_{\textrm{F}}$  = 0 is optimum. For the gains other than +1, optimum response is obtained with  $R_{\textrm{F}}$  between 500 $\Omega$  to  $1 k\Omega$ . For  $A_{\textrm{V}}$  = 2 and  $R_{\textrm{F}}$  =  $R_{\textrm{G}}$  =  $806\Omega$ , the BW is about 190MHz and the frequency response is very flat.

The EL5175 and EL5375 have a gain bandwidth product of 200MHz. For gains ≥5, its bandwidth can be predicted by using Equation 2:

$$Gain \times BW = 200MHz \tag{EQ. 2}$$

#### **Driving Capacitive Loads and Cables**

The EL5175 and EL5375 can drive 15pF capacitance in parallel with  $500\Omega$  load to ground with less than 4.5dB of peaking at a gain of +1. If less peaking is desired in applications, a small series resistor (usually between  $5\Omega$  to  $50\Omega$ ) can be placed in series with each output to eliminate most peaking. However, this will reduce the gain slightly. If the gain setting is greater than 1, the gain resistor  $R_G$  can then be chosen to make up for any gain loss, which may be created by the additional series resistor at the output.

When used as a cable driver, double termination is always recommended for reflection-free performance. For those applications, a back-termination series resistor at the amplifier's output will isolate the amplifier from the cable and allow extensive capacitive drive. However, other applications may have high capacitive loads without a back-termination resistor. Again, a small series resistor at the output can help to reduce peaking.

#### Disable/Power-Down

The EL5175 and EL5375 can be disabled and its outputs placed in a high impedance state. The turn-off time is about 1.2 $\mu$ s and the turn-on time is about 80ns. When disabled, the amplifier's supply current is reduced to 80 $\mu$ A for I<sub>S</sub>+ and 120 $\mu$ A for I<sub>S</sub>- typically, thereby effectively eliminating the



power consumption. The amplifier's power-down can be controlled by standard CMOS signal levels at the ENABLE pin. The applied logic signal is relative to the  $V_S+$  pin. Letting the  $\overline{EN}$  pin float or applying a signal that is less than 1.5V below  $V_S+$  will enable the amplifier. The amplifier will be disabled when the signal at the  $\overline{EN}$  pin is above  $V_S+$  - 0.5V. If a TTL signal is used to control the enabled/disabled function, Figure 26 could be used to convert the TTL signal to CMOS signal.

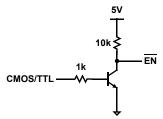


FIGURE 26. CONVERSION OF TTL SIGNAL TO CMOS SIGNAL

#### **Output Drive Capability**

The EL5175 and EL5375 have internal short circuit protection. Its typical short circuit current is ±67mA. If the output is shorted indefinitely, the power dissipation could easily increase such that the part will be destroyed. Maximum reliability is maintained if the output current never exceeds ±60mA. This limit is set by the design of the internal metal interconnections.

#### **Power Dissipation**

With the high output drive capability of the EL5175 and EL5375, it is possible to exceed the +135°C absolute maximum junction temperature under certain load current conditions. Therefore, it is important to calculate the maximum junction temperature for the application to determine if the load conditions or package types need to be modified for the amplifier to remain in the safe operating area.

The maximum power dissipation allowed in a package is determined according to Equation 3:

$$PD_{MAX} = \frac{T_{JMAX} - T_{AMAX}}{\Theta_{JA}}$$
 (EQ. 3)

- T<sub>JMAX</sub> = Maximum junction temperature
- T<sub>AMAX</sub> = Maximum ambient temperature
- $\theta_{JA}$  = Thermal resistance of the package

Assume the REF pin is tired to GND for  $V_S = \pm 5V$  application, the maximum power dissipation actually produced by an IC is the total quiescent supply current times the total power supply voltage, plus the power in the IC due to the load, or:

For sourcing, see Equation 4:

$$PD_{MAX} = \left[V_S \times I_{SMAX} + (V_S + -V_{OUT}) \times \frac{V_{OUT}}{R_{LOAD}}\right] \times i$$
 (EQ. 4)

For sinking, see Equation 5:

$$PD_{MAX} = [V_S \times I_{SMAX} + (V_{OUT} - V_S -) \times I_{LOAD}] \times i$$
 (EQ. 5)

#### Where:

- V<sub>S</sub> = Total supply voltage
- I<sub>SMAX</sub> = Maximum quiescent supply current per channel
- V<sub>OUT</sub> = Maximum output voltage of the application
- R<sub>LOAD</sub> = Load resistance
- I<sub>LOAD</sub> = Load current
- i = Number of channels

By setting the two  $PD_{MAX}$  equations equal to each other, we can solve the output current and  $R_{LOAD}$  to avoid the device overheat.

# Power Supply Bypassing and Printed Circuit Board Layout

As with any high frequency device, a good printed circuit board layout is necessary for optimum performance. Lead lengths should be as short as possible. The power supply pin must be well bypassed to reduce the risk of oscillation. For normal single supply operation, where the  $V_S$ - pin is connected to the ground plane, a single 4.7 $\mu$ F tantalum capacitor in parallel with a 0.1 $\mu$ F ceramic capacitor from  $V_S$ + to GND will suffice. This same capacitor combination should be placed at each supply pin to ground if split supplies are to be used. In this case, the  $V_S$ - pin becomes the negative supply rail.

For good AC performance, parasitic capacitance should be kept to a minimum. Use of wire-wound resistors should be avoided because of their additional series inductance. Use of sockets should also be avoided if possible. Sockets add parasitic inductance and capacitance that can result in compromised performance. Minimizing parasitic capacitance at the amplifier's inverting input pin is very important. The feedback resistor should be placed very close to the inverting input pin. Strip line design techniques are recommended for the signal traces.



## **Typical Applications**

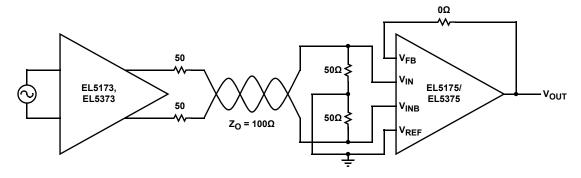


FIGURE 27. TWISTED PAIR CABLE RECEIVER

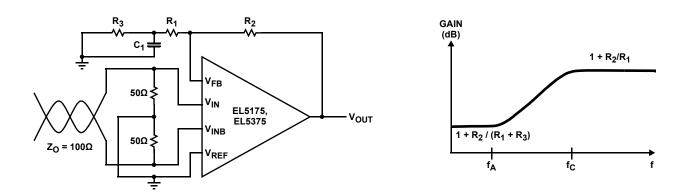


FIGURE 28. COMPENSATED LINE RECEIVER

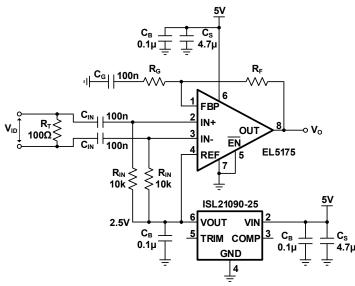


FIGURE 29. Single Supply Operation



As the signal is transmitted through a cable, the high frequency signal will be attenuated. One way to compensate this loss is to boost the high frequency gain at the receiver side.

#### Level Shifter and Signal Summer

The EL5175 and EL5375 contains two pairs of differential pair input stages. It makes the inputs all high impedance. To take advantage of the two high impedance inputs, the EL5175 and EL5375 can be used as a signal summer to add two signals together. One signal can be applied to  $V_{\mbox{\footnotesize{IN}}^+}$ ; the second signal can be applied to REF and  $V_{\mbox{\footnotesize{IN}}^-}$  is ground. The output is equal to Equation 6:

$$V_O = (V_{IN} + V_{REF}) \times Gain$$
 (EQ. 6)

Also, the EL5175 and EL5375 can be used as a level shifter by applying a level control signal to the REF input.



## **Revision History**

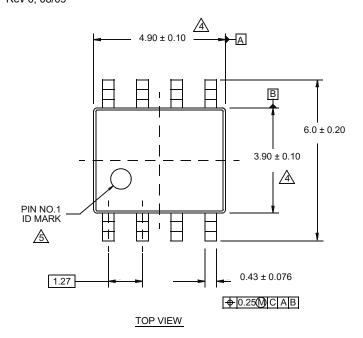
The revision history provided is for informational purposes only and is believed to be accurate, but not warranted. Please visit our website to make sure you have the latest revision.

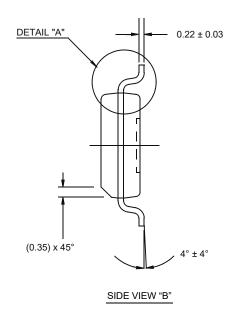
DATE	REVISION	CHANGE
Aug 7, 2020	8.00	Added Related Literature section. Updated Ordering Information table by removing retired parts, adding tape and reel information, and updating notes. Added Figure 29. Added Revision history section Replaced the following PODs: Old POD MDP0027 with new POD M8.15E Old POD MDP0043 with new POD M8.118A

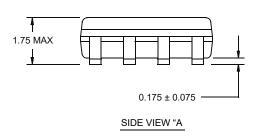
## Package Outline Drawings

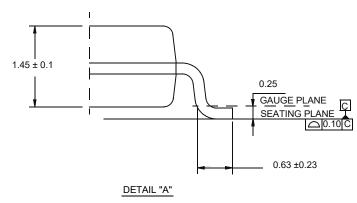
8 Lead Narrow Body Small Outline Plastic Package Rev 0, 08/09

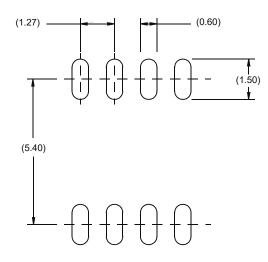
For the most recent package outline drawing, see M8.15E.











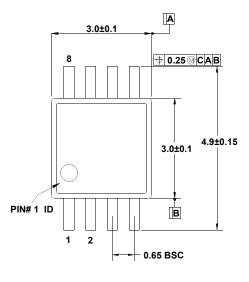
TYPICAL RECOMMENDED LAND PATTERN

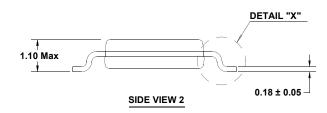
- 1. Dimensions are in millimeters. Dimensions in ( ) for Reference Only.
- 2. Dimensioning and tolerancing conform to AMSE Y14.5m-1994.
- 3. Unless otherwise specified, tolerance : Decimal  $\pm 0.05$
- Dimension does not include interlead flash or protrusions. Interlead flash or protrusions shall not exceed 0.25mm per side.
- 5. The pin #1 identifier may be either a mold or mark feature.
- Reference to JEDEC MS-012.

M8.118A

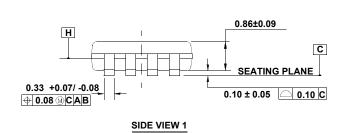
8 Lead Mini Small Outline Plastic Package (MSOP) Rev 0, 9/09

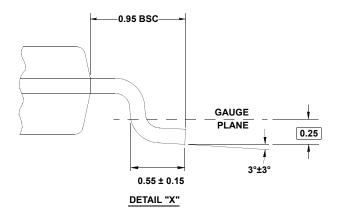
For the most recent package outline drawing, see M8.118A.

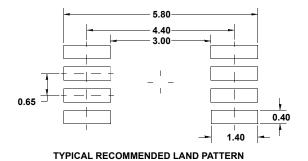




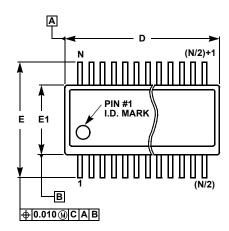
TOP VIEW

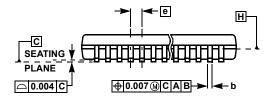


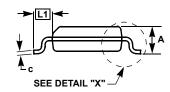


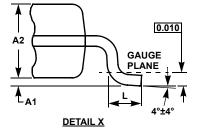


- 1. Dimensions are in millimeters.
- Dimensioning and tolerancing conform to JEDEC MO-187-AA and AMSE Y14.5m-1994.
- Plastic or metal protrusions of 0.15mm max per side are not included.
- Plastic interlead protrusions of 0.25mm max per side are not included.
- 5. Dimensions "D" and "E1" are measured at Datum Plane "H".
- 6. This replaces existing drawing # MDP0043 MSOP 8L.









For the most recent package outline drawing, see MDP0040.

#### **MDP0040**

Quarter Size Outline Plastic Packages Family (QSOP)

			_	•	
		INCHES			
SYMBOL	QSOP16	QSOP24	QSOP28	TOLERANCE	NOTES
Α	0.068	0.068	0.068	Max.	-
A1	0.006	0.006	0.006	±0.002	-
A2	0.056	0.056	0.056	±0.004	-
b	0.010	0.010	0.010	±0.002	-
С	0.008	800.0	0.008	±0.001	-
D	0.193	0.341	0.390	±0.004	1, 3
E	0.236	0.236	0.236	±0.008	-
E1	0.154	0.154	0.154	±0.004	2, 3
е	0.025	0.025	0.025	Basic	-
L	0.025	0.025	0.025	±0.009	-
L1	0.041	0.041	0.041	Basic	-
N	16	24	28	Reference	-

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- 4. Plastic or metal protrusions of 0.006" maximum per side are not included.
- 5. Plastic interlead protrusions of 0.010" maximum per side are not included
- 6. Dimensions "D" and "E1" are measured at Datum Plane "H".
- 7. Dimensioning and tolerancing per ASME Y14.5M-1994.

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